

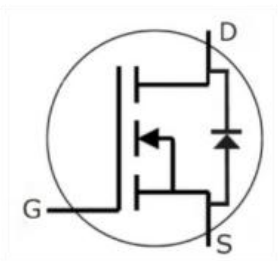
SG2M500120BH



TriQSiC™ 1200V Silicon Carbide Power MOSFET G2 (N Channel Enhancement)

Features

- Softer $R_{DS(on)}$ v/s Temperature Dependency
- Smaller $R_{g(int)}$ and Lower Q_g
- Low Device Capacitances (C_{oss}, C_{rss})
- Superior Cost-Performance Index
- Robust Body Diode with Low V_F and Low Q_{rr}
- Industry-Leading UIL&Short-Circuit Robustness



Benefits

- Compatible with Commercial Gate Drivers
- Reduced Ringing
- Faster and More Efficient Switching
- Higher System Reliability
- Lesser Switching Spikes and Lower Losses

Part number	Die size (W x L) mm
SG2M500120BH	1.39*1.39

Applications

- Auxiliary Power Supply
- Infrastructure Chargers
- Piezo Drivers
- Pulsed Power

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS} ($T_C=25^{\circ}C$, $R_{th(j-c),max} \leq 3^{\circ}C/W$)	$R_{DS(on), typ}$ ($V_{GS} = 15V, I_D = 2.5A,$ $T_J = 25^{\circ}C$)	$T_{J,max}$
SG2M500120BH	1200V	8A	470mΩ	175℃

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1、Maximum ratings

Table 2 Maximum rating ($T_c = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{DS,max}$	Drain source voltage	1200	V	$V_{GS} = 0\text{V}$, $I_D = 100\mu\text{A}$	
$V_{GS,max}$	Gate source voltage	-8 / +19	V	Absolute maximum values	Note1
V_{GSop}	Gate source voltage	-4 / +15	V	Recommended operational values	
I_D	Continuous drain current	8	A	$V_{GS} = 15\text{V}$, $T_C = 25^{\circ}\text{C}$	
		6		$V_{GS} = 15\text{V}$, $T_C = 100^{\circ}\text{C}$	
$I_{D(pulse)}$	Pulsed drain current	16	A	Pulse width t_p limited by $T_{J,max}$	
T_J, T_{stg}	Operating Junction and storage temperature	-55 to +175	$^{\circ}\text{C}$		

Note 1: when using MOSFET Body Diode $V_{GS,max} = -4 / +19\text{V}$

2、Electrical characteristics

2.1 Static characteristics

Table 4 Static characteristics (Tc = 25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-source breakdown voltage	1200	-	-	V	$V_{GS} = 0V, I_D = 100\mu A$	
$V_{GS(th)}$	Gate threshold voltage	2.3	2.8	3.6	V	$V_{DS} = V_{GS}, I_D = 700\mu A$	Fig.11
		-	2.2	-	V	$V_{DS} = V_{GS}, I_D = 700\mu A,$ $T_J = 175^\circ C$	
I_{DSS}	Zero gate voltage drain current	-	-	10	μA	$V_{DS} = 1200V, V_{GS} = 0V$	
I_{GSS}	Gate source leakage current	-	-	100	nA	$V_{GS} = 15V, V_{DS} = 0V$	
$R_{DS(on)}$	Current drain-source on-state resistance	-	470	650	m Ω	$V_{GS} = 15V, I_D = 2.5A$	Fig.4,5, 6
		-	765	-		$V_{GS} = 15V, I_D = 2.5A,$ $T_J = 175^\circ C$	
g_{fs}	Transconductance	-	1.8	-	S	$V_{DS} = 20V, I_D = 2.5A$	Fig.7
		-	1.6	-		$V_{DS} = 20V, I_D = 2.5A,$ $T_J = 175^\circ C$	
$R_{g,int}$	Intenal gate resistance	-	22	-	Ω	$V_{AC} = 25mV, f = 1MHz,$ open drain	

2.2 Dynamic characteristics

Table 5 Dynamic characteristics (Tc = 25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
C_{iss}	Input capacitance	-	167	-	pF	$V_{DS} = 1000V, V_{GS} = 0V$ $T_J = 25^\circ C, V_{AC} = 25mV$ $f = 100kHz$	Fig.17, 18
C_{oss}	Output capacitance	-	13	-			
C_{rss}	Reverse capacitance	-	0.8	-			
E_{oss}	Coss stored energy	-	6.8	-	μJ		Fig.16

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Q_{gs}	Gate source charge	-	2.1	-	nC	$V_{DS} = 800V$, $V_{GS} = -4/+15V$ $I_D = 2.5A$	
Q_{gd}	Gate drain charge	-	3.6	-			
Q_g	Gate charge	-	9.6	-			

2.3 Switching characteristics

Table 6 Dynamic characteristics($T_c = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
E _{on}	Turn on switching energy	-	52	-	μJ	V _{DS} = 800V, V _{GS} = -4/+15V I _D = 2.5A, R _g = 2.5Ω L = 120μH	
E _{off}	Turn off switching energy	-	1.1	-			
t _{d (on)}	Turn on delay time	-	8	-	ns		
t _r	Rise time	-	8.3	-			
t _{d (off)}	Turn off delay time	-	17	-			
t _f	Fall time	-	21	-			

Table 7 Body diode characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode forward voltage	-	3.6	-	V	$V_{GS} = -4V$, $I_{SD} = 1.25A$	Fig.8,9, 10
		-	3.3	-	V	$V_{GS} = -4V$, $I_{SD} = 1.25A$ $T_J = 175^\circ C$	
I_S	Continuous diode forward current	-	8	-	A	$V_{GS} = -4V$, $T_c = 25^\circ C$	Note2
t_{rr}	Reverse recovery time	-	9	-	ns	$V_R = 800V$, $V_{GS} = -4V$ $I_{SD} = 2.5A$ $di/dt = 1960A/\mu s$ $T_J = 175^\circ C$	
Q_{rr}	Reverse recovery charge	-	44	-	nC		
I_{rrm}	Peak reverse recovery current	-	8	-	A		

Note 2: When using SiC Body Diode the maximum recommended $V_{GS} = -4V$

3、Electrical characteristic diagrams

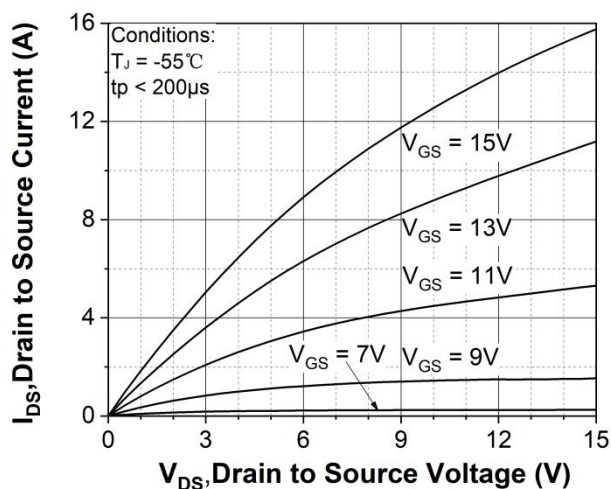


Figure 1. Output characteristics $T_J = -55^\circ\text{C}$

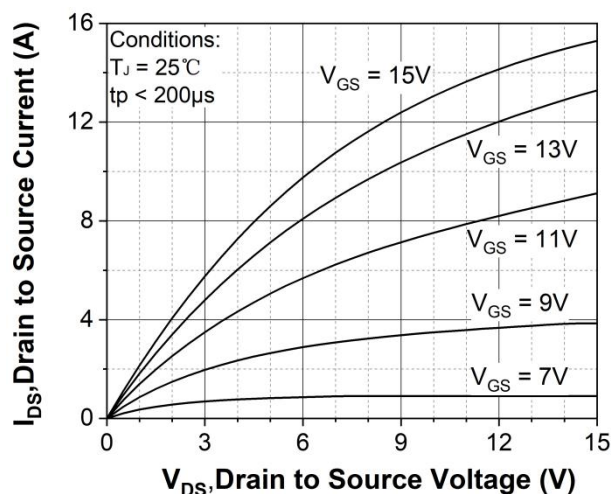


Figure 2. Output characteristics $T_J = 25^\circ\text{C}$

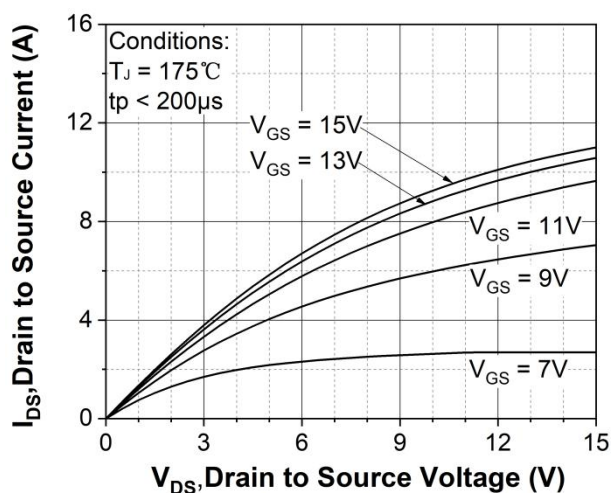


Figure 3. Output characteristics $T_J = 175^\circ\text{C}$

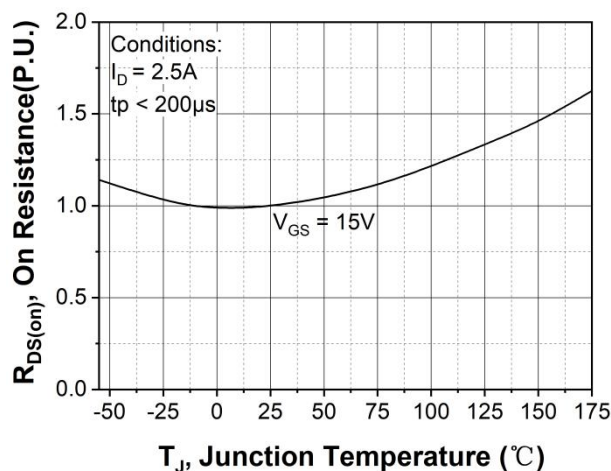


Figure 4. Normalized on-resistance vs. temperature

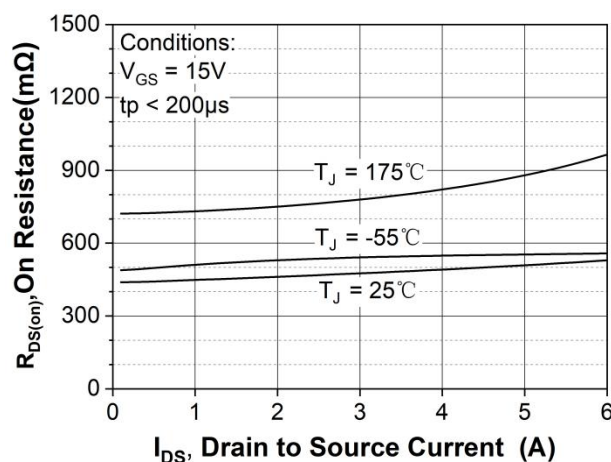


Figure 5. On-resistance vs. drain current
for various temperatures

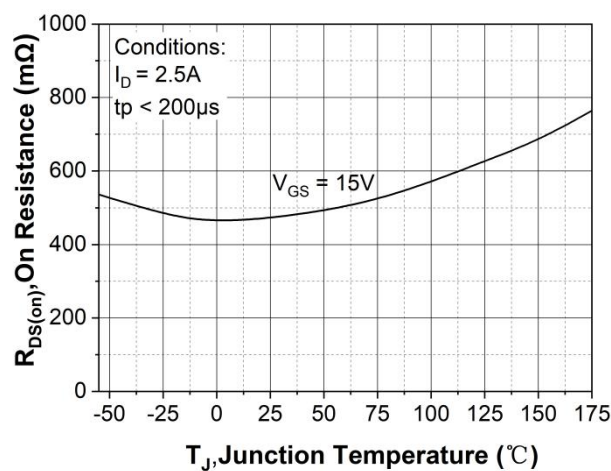


Figure 6. On-resistance vs. Temperature
for various gate voltages

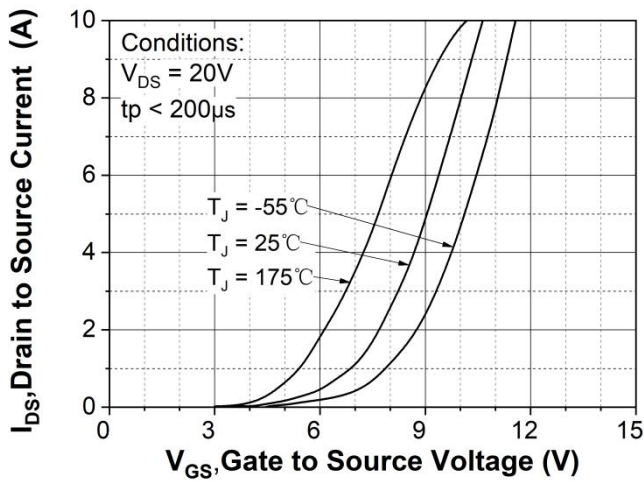


Figure 7. Transfer characteristic for various junction temperatures

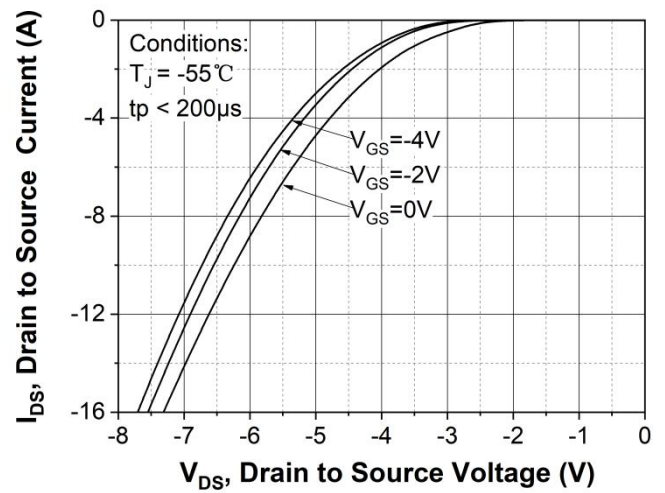


Figure 8. Body diode characteristic at $T_J = -55^\circ\text{C}$

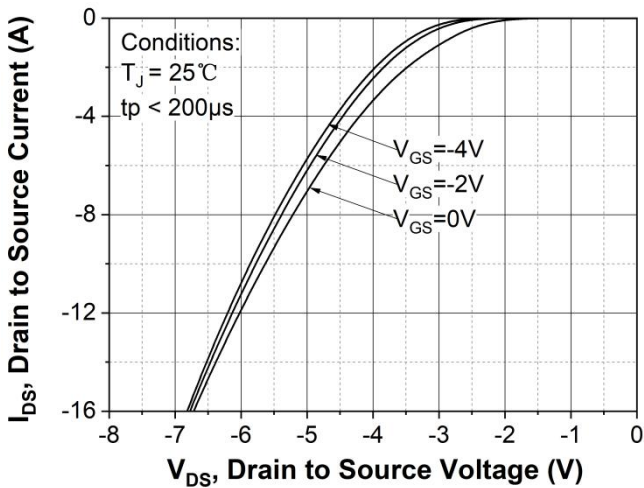


Figure 9. Body diode characteristic at $T_J = 25^\circ\text{C}$

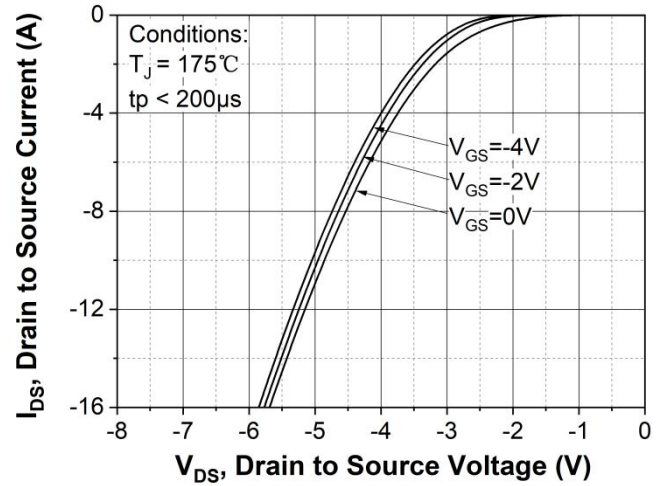


Figure 10. Body diode characteristic at $T_J = 175^\circ\text{C}$

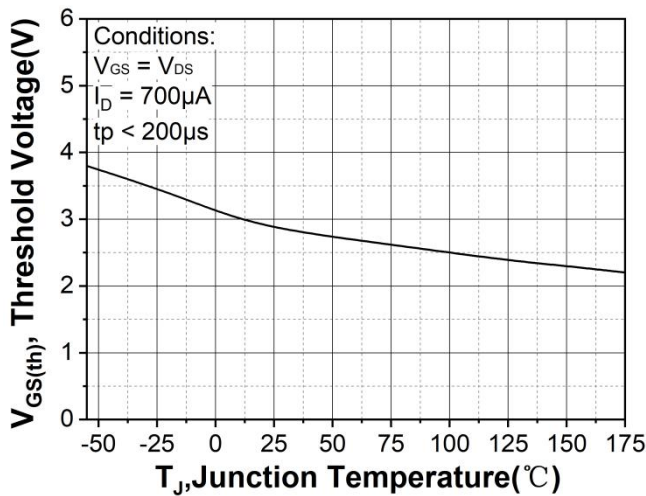


Figure 11. Threshold voltage vs. temperature

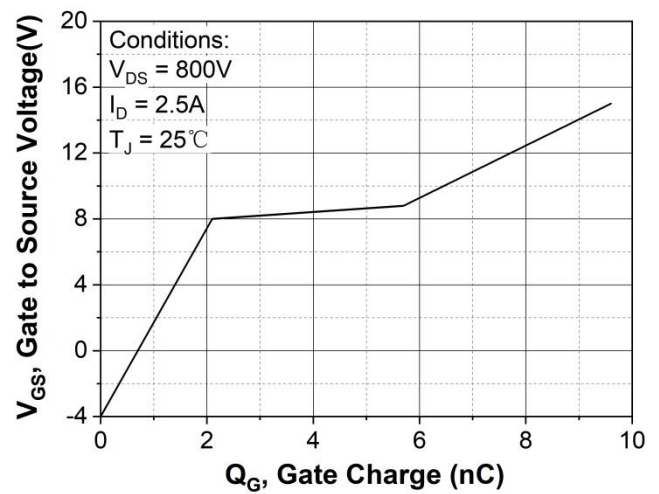


Figure 12. Gate charge characteristic

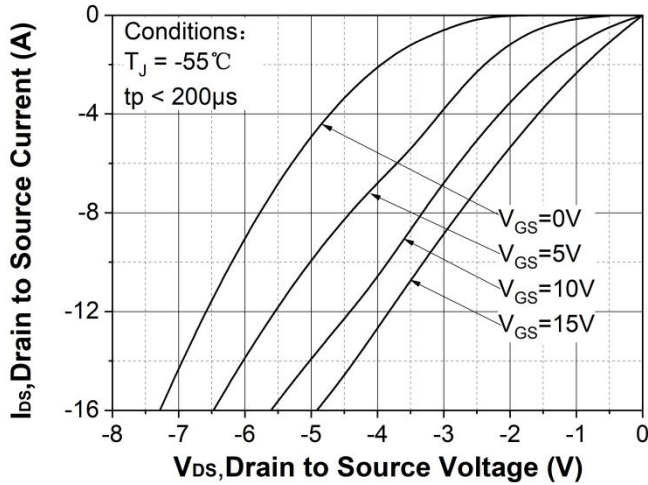


Figure 13. 3rd quadrant characteristic at $T_J = -55\text{ }^{\circ}\text{C}$

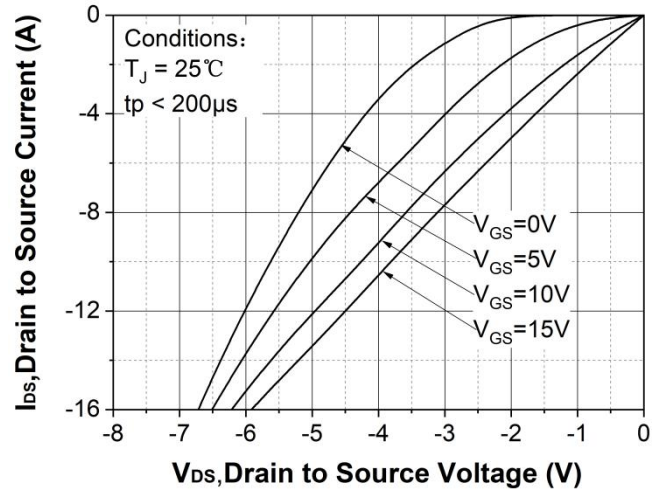


Figure 14. 3rd quadrant characteristic at $T_J = 25\text{ }^{\circ}\text{C}$

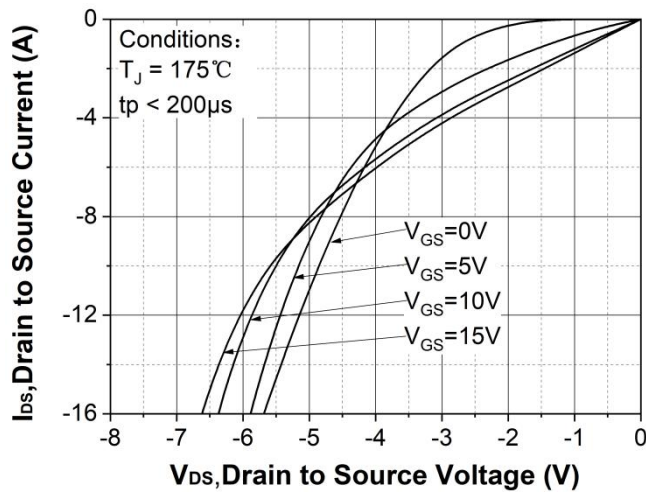


Figure 15. 3rd quadrant characteristic at $T_J = 175\text{ }^{\circ}\text{C}$

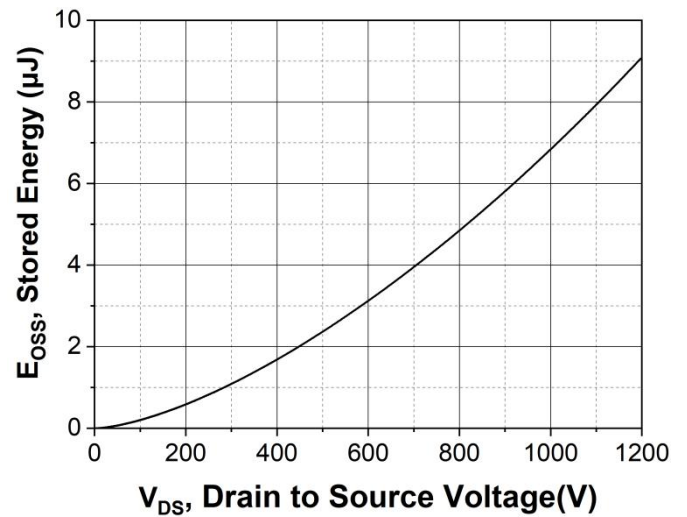


Figure 16. Output capacitor stored energy

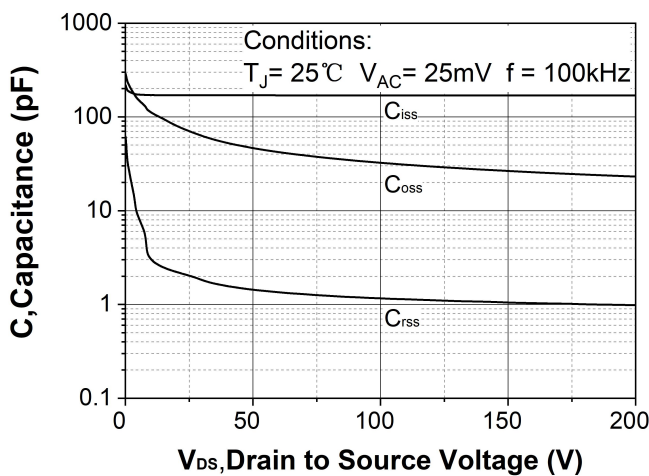


Figure 17. Capacitances vs. drain-source voltage (0 - 200V)

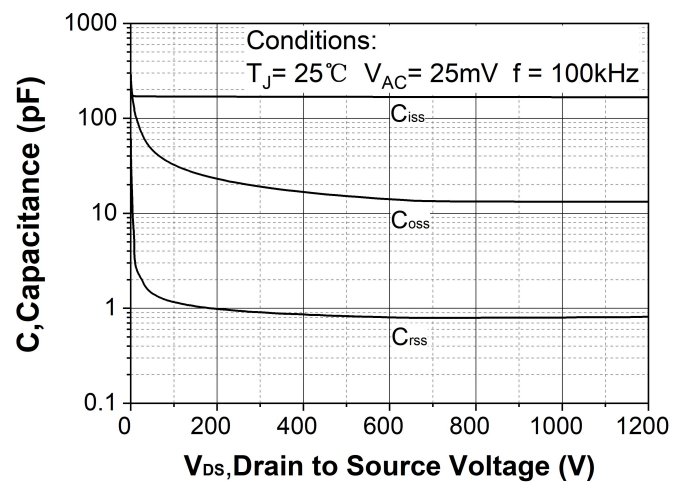


Figure 18. Capacitances vs. drain-source voltage (0 - 1200V)

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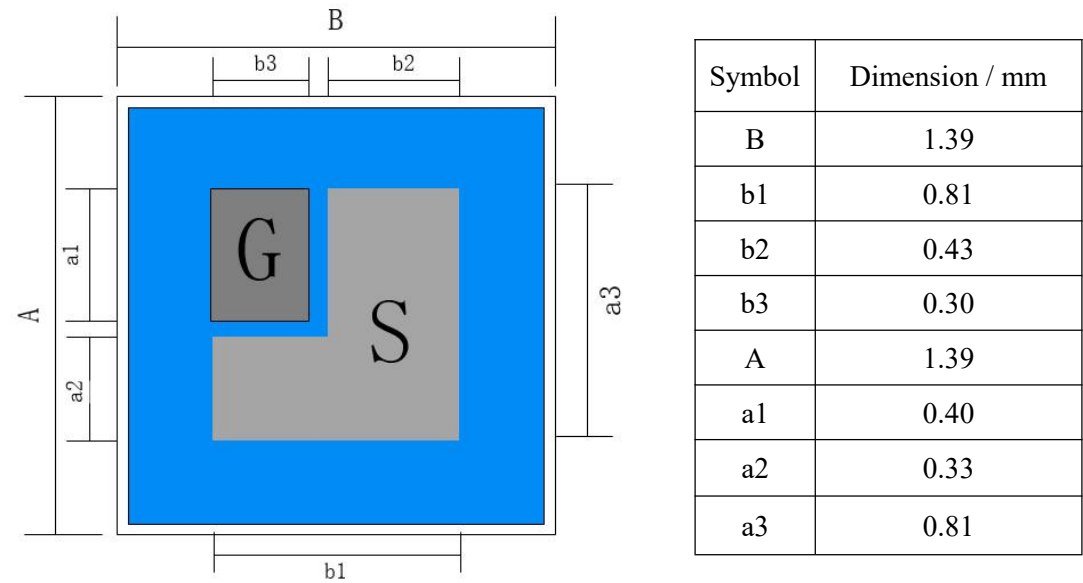
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4、Mechanical parameters

4.1 Dimensions and metallization

Parameter	Typical value	Unit	Metallization
Die size (W x L)	1.39 * 1.39	mm	
Gate pad size (W x L)	0.40 * 0.30	mm	
Die thickness	175	μm	
Top side (source gate) metallization	4	μm	Al
Back side (drain) metallization	1	μm	Ag

4.2 Layout



5、 Test conditions

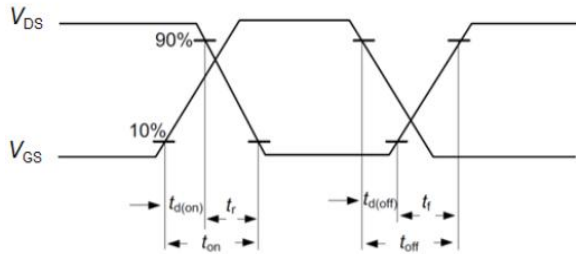


Figure A. Definition of switching times

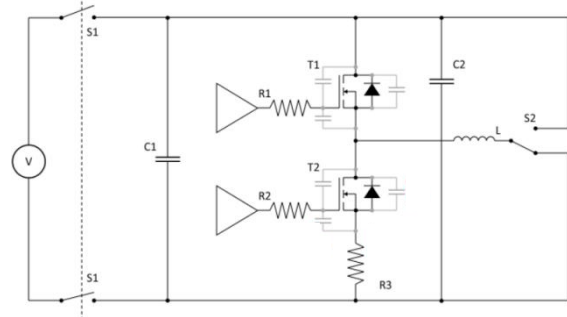


Figure B. Dynamic test circuit

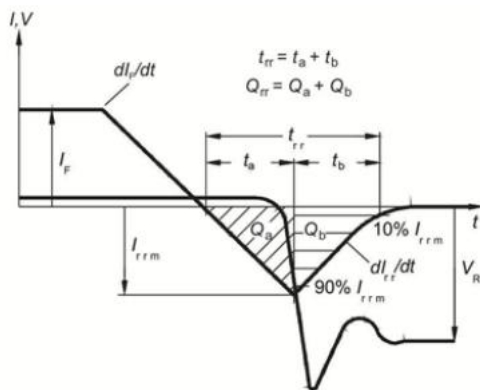


Figure C. Definition of body diode switching characteristics

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2025-09-19	Final	--

Attention

1. Rohs compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/ EC (RoHS2), as implemented January 2, 2013.

2. REACH compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Sichain representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

3. With respect to information regarding the application of the product, Sichain hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

4. Any information given in this documents subject to customer's compliance with its obligations and any applicable legal requirements, norms and standards concerning any use of the product of Sichain in any customer's applications.

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6. Due to technical requirements products may contain dangerous substances. For information on the types in question please contact Sichain office.

7. Except as otherwise explicitly approved by Sichain in a written document signed by authorized representatives of Sichain, Sichain' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

8. For use of our products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a Sichain representatives, for example but not limited to: transportation equipment, primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, and power transmission systems.